

MOS FIELD EFFECT TRANSISTOR 2SK4035

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

2SK4035 is the best switching element for the DC-DC converter usage from 24 to 48 V in the direct current input voltage. It excels in the switching characteristics in low on-state resistance and because it is the small size surface mounting externals, is the best for the high-speed switching usage of the equipment that promotes the automation of space-saving and mounting.

FEATURES

- Low input capacitance Ciss = 74 pF TYP.
- Low on-state resistance $R_{DS(on)} = 4.5 \Omega MAX. (V_{GS} = 10 V, I_{D} = 0.25 A)$
- Small and surface mount package (SC-96)

ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK4035	SC-96 (Mini Mold Thin Type)		
2SK4035-A Note	SC-96 (Mini Mold Thin Type)		

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

Marking: XP

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	250	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±30	V
Drain Current (DC) (T _A = 25°C)	ID(DC)	±0.5	Α
Drain Current (pulse) Note1	I _{D(pulse)}	±2.0	Α
Total Power Dissipation (T _A = 25°C)	P _{T1}	0.2	W
Total Power Dissipation (T _A = 25°C) Note2	Рт2	1.25	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tsta	-55 to +150	°C

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

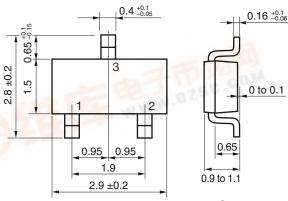
2. Mounted on FR-4 board of 50 mm x 50 mm x 1.6 mm, $t \le 5$ sec

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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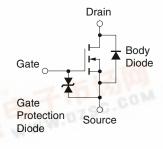
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PACKAGE DRAWING (Unit: mm)



- 1. Gate
- 2. Source
- 3. Drain

EQUIVALENT CIRCUIT



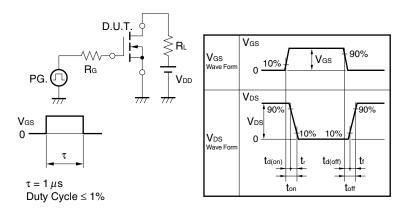


ELECTRICAL CHARACTERISTICS (TA = 25°C)

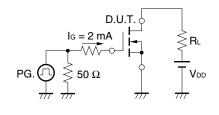
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 250 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	2.5	3.5	4.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 0.25 A	0.2	0.5		S
Drain to Source On-state Resistance Note	RDS(on)	V _{GS} = 10 V, I _D = 0.25 A		3.2	4.5	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		74		pF
Output Capacitance	Coss	V _{GS} = 0 V		16		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		7		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 125 V, I _D = 0.25 A		7		ns
Rise Time	tr	V _{GS} = 10 V		5		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		12		ns
Fall Time	t _f			40		ns
Total Gate Charge	Q _G	V _{DD} = 200 V		4		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		0.9		nC
Gate to Drain Charge	Q _{GD}	I _D = 0.5 A		2		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 0.5 A, V _{GS} = 0 V		0.84		V
Reverse Recovery Time	trr	I _F = 0.5 A, V _{GS} = 0 V		42		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		57		nC

Note Pulsed

TEST CIRCUIT 1 SWITCHING TIME

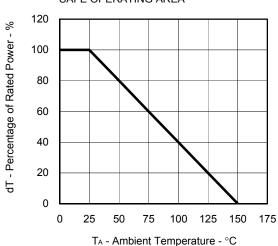


TEST CIRCUIT 2 GATE CHARGE

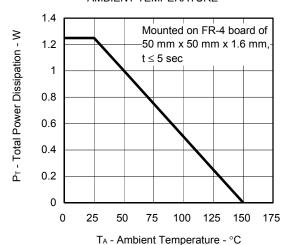


TYPICAL CHARACTERISTICS (TA = 25°C)

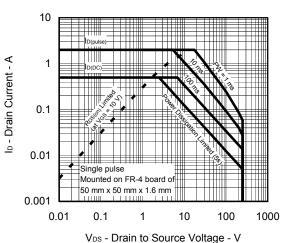
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



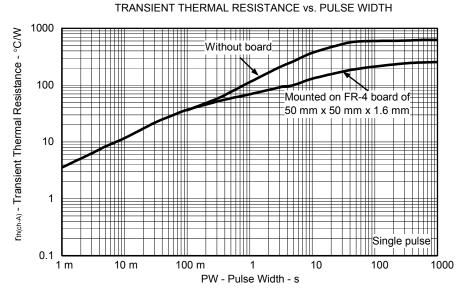
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD BIAS SAFE OPERATING AREA



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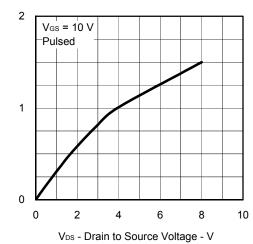


lo - Drain Current - A

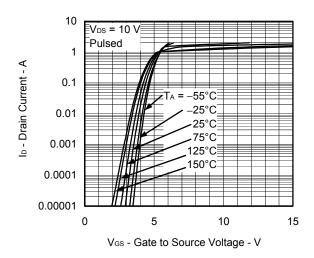
VGS(off) - Gate Cut-off Voltage - V

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

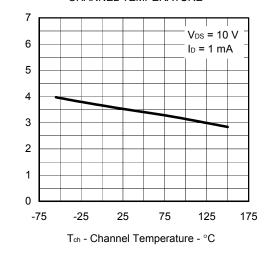
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



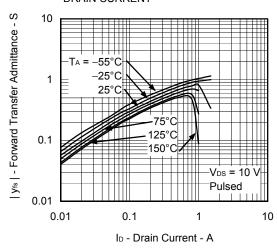
FORWARD TRANSFER CHARACTERISTICS



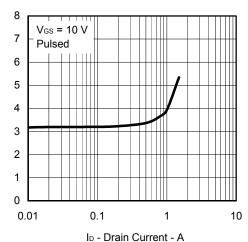
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



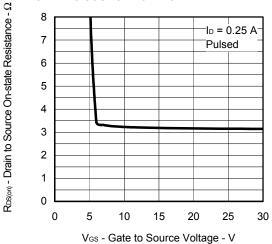
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

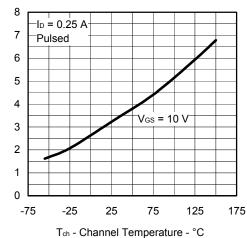


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

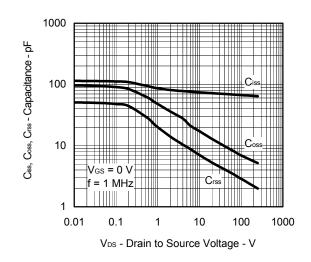


 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

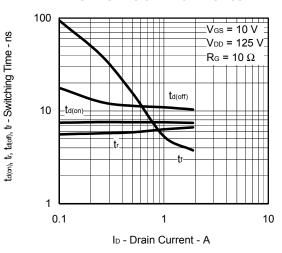
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



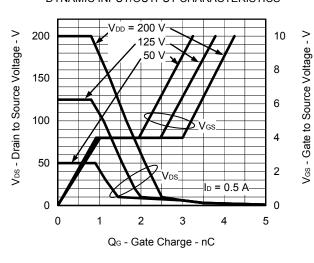
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



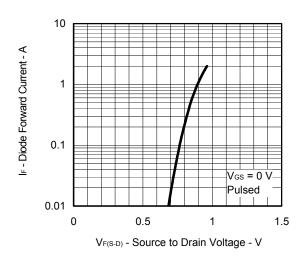
SWITCHING CHARACTERISTICS



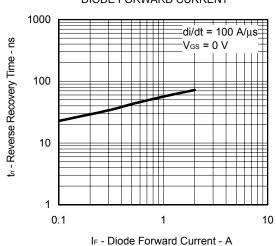
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



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